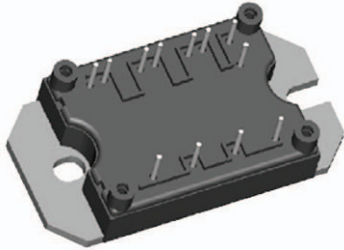



“Half Bridge” IGBT MTP (Ultrafast NPT IGBT), 80 A



MTP

PRODUCT SUMMARY	
V_{CES}	1200 V
$V_{CE(on)}$ typical at $V_{GE} = 15$ V	3.36 V
I_C at $T_C = 25$ °C	80 A
Speed	8 kHz to 30 kHz
Package	MTP
Circuit	Half bridge

FEATURES

- Ultrafast Non Punch Through (NPT) technology
- Positive $V_{CE(on)}$ temperature coefficient
- 10 μ s short circuit capability
- Square RBSOA
- HEXFRED® antiparallel diodes with ultrasoft reverse recovery and low V_F
- Al_2O_3 DBC
- Optional SMD thermistor (NTC)
- Very low stray inductance design for high speed operation
- UL approved file E78996 
- Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS*
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non-RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details.

BENEFITS

- Optimized for welding, UPS and SMPS applications
- Rugged with ultrafast performance
- Benchmark efficiency above 20 kHz
- Outstanding ZVS and hard switching operation
- Low EMI, requires less snubbing
- Excellent current sharing in parallel operation
- Direct mounting to heatsink
- PCB solderable terminals
- Very low junction to case thermal resistance

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter breakdown voltage	V_{CES}		1200	V
Continuous collector current	I_C	$T_C = 25$ °C	80	A
		$T_C = 104$ °C	40	
Pulsed collector current	I_{CM}		160	
Clamped inductive load current	I_{LM}		160	
Diode continuous forward current	I_F	$T_C = 105$ °C	21	
Diode maximum forward current	I_{FM}		160	
Gate to emitter voltage	V_{GE}		± 20	V
RMS isolation voltage	V_{ISOL}	Any terminal to case, $t = 1$ min	2500	
Maximum power dissipation (only IGBT)	P_D	$T_C = 25$ °C	463	W
		$T_C = 100$ °C	185	



ELECTRICAL SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$	1200	-	-	V
Temperature coefficient of breakdown voltage	$\Delta V_{(BR)CES}/\Delta T_J$	$V_{GE} = 0\text{ V}, I_C = 3\text{ mA}$ (25 °C to 125 °C)	-	+1.1	-	V/°C
Collector to emitter saturation voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}, I_C = 40\text{ A}$	-	3.36	3.59	V
		$V_{GE} = 15\text{ V}, I_C = 80\text{ A}$	-	4.53	4.91	
		$V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 150\text{ }^\circ\text{C}$	-	3.88	4.10	
		$V_{GE} = 15\text{ V}, I_C = 80\text{ A}, T_J = 150\text{ }^\circ\text{C}$	-	5.35	5.68	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_C = 500\text{ }\mu\text{A}$	4	-	6	
Temperature coefficient of threshold voltage	$V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}, I_C = 1\text{ mA}$ (25 °C to 125 °C)	-	-12	-	mV/°C
Transconductance	g_{fe}	$V_{CE} = 50\text{ V}, I_C = 40\text{ A}, PW = 80\text{ }\mu\text{s}$	-	35	-	S
Zero gate voltage collector current	I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 25\text{ }^\circ\text{C}$	-	-	250	μA
		$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	0.4	1.0	mA
		$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 150\text{ }^\circ\text{C}$	-	0.2	10	
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}$	-	-	± 250	nA

SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total gate charge (turn-on)	Q_g	$I_C = 40\text{ A}$	-	399	599	nC
Gate to emitter charge (turn-on)	Q_{ge}	$V_{CC} = 600\text{ V}$	-	43	65	
Gate to collector charge (turn-on)	Q_{gc}	$V_{GE} = 15\text{ V}$	-	187	281	
Turn-on switching loss	E_{on}	$V_{CC} = 600\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}, R_g = 5\text{ }\Omega, L = 200\text{ }\mu\text{H}, T_J = 25\text{ }^\circ\text{C},$ energy losses include tail and diode reverse recovery	-	1.14	1.71	mJ
Turn-off switching loss	E_{off}		-	1.35	2.02	
Total switching loss	E_{tot}		-	2.49	3.73	
Turn-on switching loss	E_{on}		$V_{CC} = 600\text{ V}, I_C = 40\text{ A}, V_{GE} = 15\text{ V}, R_g = 5\text{ }\Omega, L = 200\text{ }\mu\text{H}, T_J = 125\text{ }^\circ\text{C},$ energy losses include tail and diode reverse recovery	-	1.60	
Turn-off switching loss	E_{off}		-	1.62	2.43	
Total switching loss	E_{tot}		-	3.22	4.82	
Input capacitance	C_{ies}	$V_{GE} = 0\text{ V}$	-	5521	8282	pF
Output capacitance	C_{oes}	$V_{CC} = 30\text{ V}$	-	380	570	
Reverse transfer capacitance	C_{res}	$f = 1.0\text{ MHz}$	-	171	257	
Reverse bias safe operating area	RBSOA	$T_J = 150\text{ }^\circ\text{C}, I_C = 160\text{ A}$ $V_{CC} = 1000\text{ V}, V_p = 1200\text{ V}$ $R_g = 5\text{ }\Omega, V_{GE} = +15\text{ V to }0\text{ V}$	Fullsquare			
Short circuit safe operating area	SCSOA	$T_J = 150\text{ }^\circ\text{C},$ $V_{CC} = 900\text{ V}, V_p = 1200\text{ V}$ $R_g = 5\text{ }\Omega, V_{GE} = +15\text{ V to }0\text{ V}$	10	-	-	μs



DIODE SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Diode forward voltage drop	V_{FM}	$I_C = 40\text{ A}$	-	2.98	3.38	V
		$I_C = 80\text{ A}$	-	3.90	4.41	
		$I_C = 40\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	3.08	3.39	
		$I_C = 80\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	4.29	4.72	
		$I_C = 40\text{ A}, T_J = 150\text{ }^\circ\text{C}$	-	3.12	3.42	
Reverse recovery energy of the diode	E_{rec}	$V_{GE} = 15\text{ V}, R_g = 5\text{ }\Omega, L = 200\text{ }\mu\text{H}$ $V_{CC} = 600\text{ V}, I_C = 40\text{ A}$ $T_J = 125\text{ }^\circ\text{C}$	-	574	861	μJ
Diode reverse recovery time	t_{rr}		-	120	180	ns
Peak reverse recovery current	I_{rr}		-	43	65	A

THERMISTOR SPECIFICATIONS (40MT120UHTAPbF only)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Resistance	$R_0^{(1)}$	$T_0 = 25\text{ }^\circ\text{C}$	-	30	-	$\text{k}\Omega$
Sensitivity index of the thermistor material	$\beta^{(1)(2)}$	$T_0 = 25\text{ }^\circ\text{C}$ $T_1 = 85\text{ }^\circ\text{C}$	-	4000	-	K

Notes

(1) T_0, T_1 are thermistor's temperatures

(2) $\frac{R_0}{R_1} = \exp\left[\beta\left(\frac{1}{T_0} - \frac{1}{T_1}\right)\right]$, temperature in Kelvin

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Operating junction temperature range	T_J		-40	-	150	$^\circ\text{C}$
Storage temperature range	T_{Stg}		-40	-	125	
Junction to case	IGBT	R_{thJC}	-	-	0.29	$^\circ\text{C/W}$
	Diode		-	-	0.61	
Case to sink per module	R_{thCS}	Heatsink compound thermal conductivity = 1 W/mK	-	0.06	-	
Clearance ⁽¹⁾		External shortest distance in air between 2 terminals	5.5	-	-	mm
Creepage ⁽²⁾		Shortest distance along external surface of the insulating material between 2 terminals	8	-	-	
Mounting torque to heatsink		A mounting compound is recommended and the torque should be checked after 3 hours to allow for the spread of the compound. Lubricated threads.	3 ± 10 %			Nm
Weight			66			g

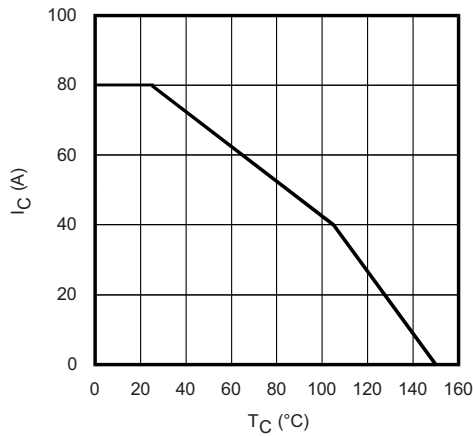


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

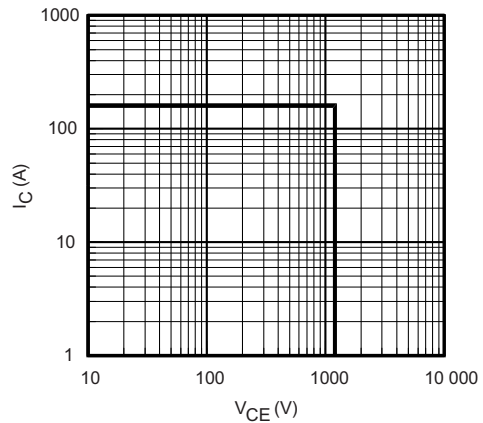


Fig. 4 - Reverse BIAS SOA
T_J = 150 °C; V_{GE} = 15 V

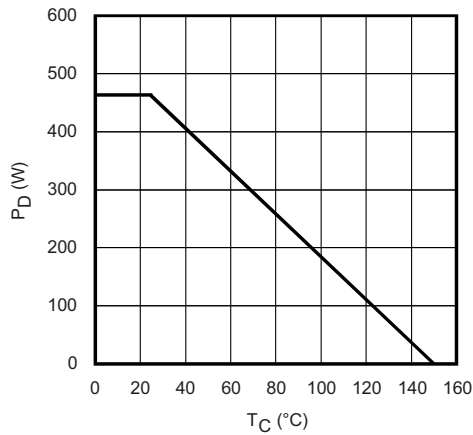


Fig. 2 - Power Dissipation vs. Case Temperature

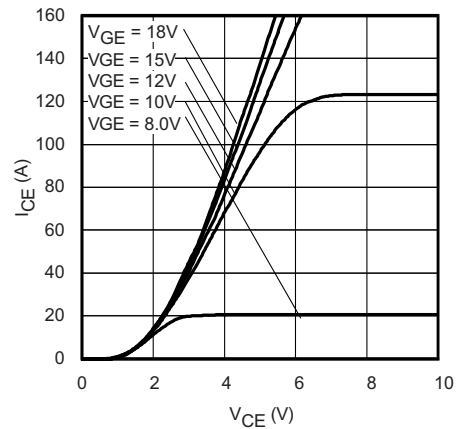


Fig. 5 - Typical IGBT Output Characteristics
T_J = - 40 °C; t_p = 80 μs

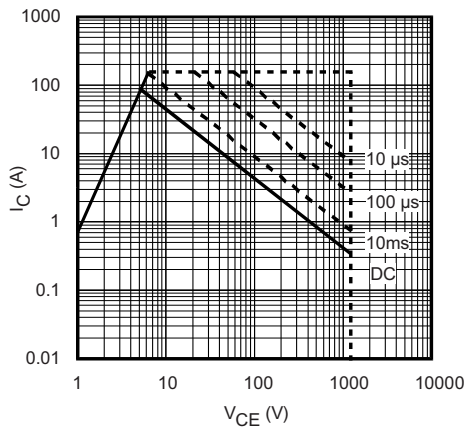


Fig. 3 - Forward SOA
T_C = 25 °C; T_J ≤ 150 °C

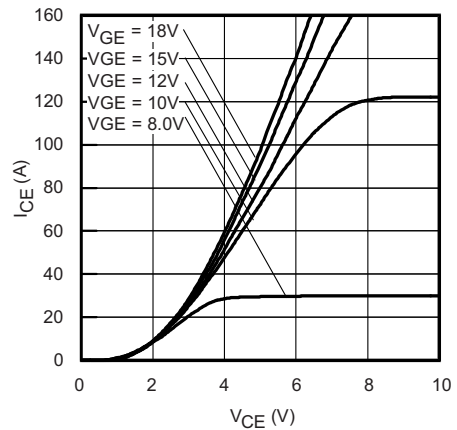


Fig. 6 - Typical IGBT Output Characteristics
T_J = 25 °C; t_p = 80 μs

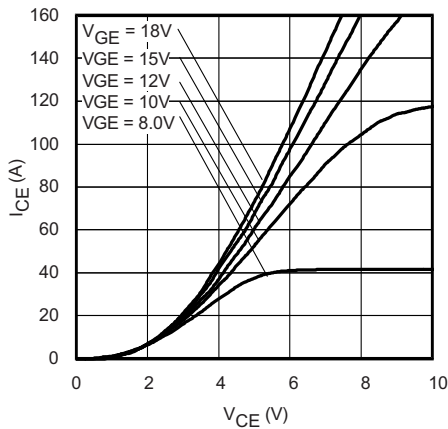


Fig. 7 - Typical IGBT Output Characteristics
 $T_J = 125^\circ\text{C}$; $t_p = 80\ \mu\text{s}$

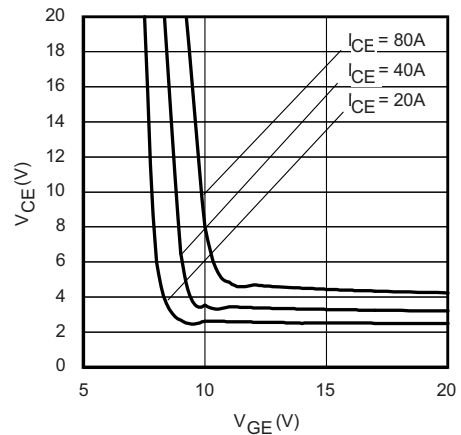


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

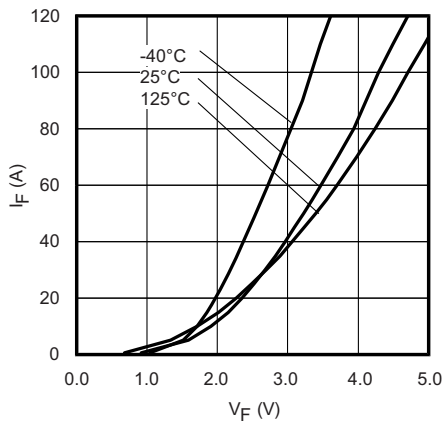


Fig. 8 - Typical Diode Forward Characteristics
 $t_p = 80\ \mu\text{s}$

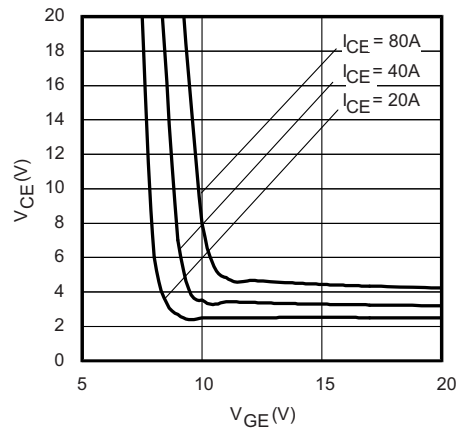


Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 125^\circ\text{C}$

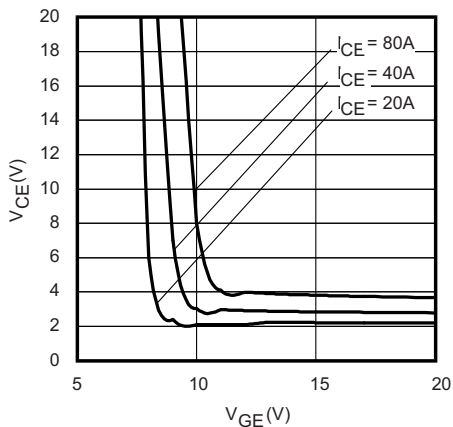


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^\circ\text{C}$

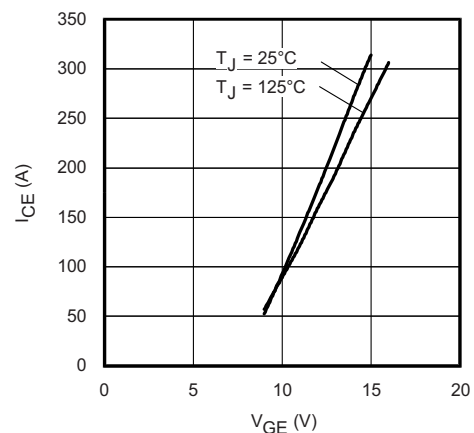


Fig. 12 - Typical Transfer Characteristics
 $V_{CE} = 50\ \text{V}$; $t_p = 10\ \mu\text{s}$

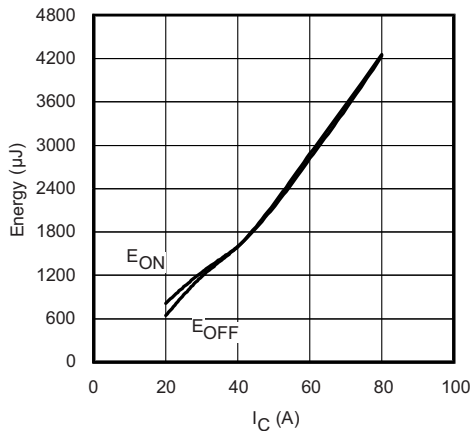


Fig. 13 - Typical Energy Loss vs. I_C
 T_J = 125 °C; L = 250 μH; V_{CE} = 400 V
 R_g = 5 Ω; V_{GE} = 15 V

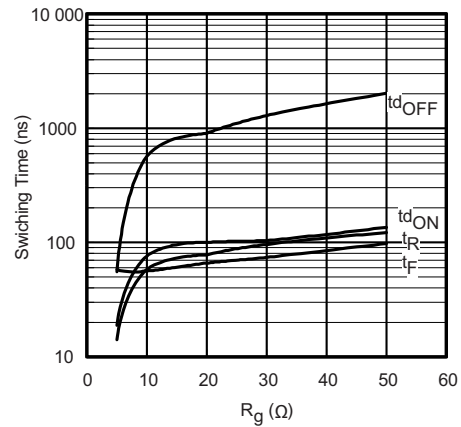


Fig. 16 - Typical Switching Time vs. R_g
 T_J = 150 °C; L = 250 μH; V_{CE} = 600 V
 I_{CE} = 40 A; V_{GE} = 15 V

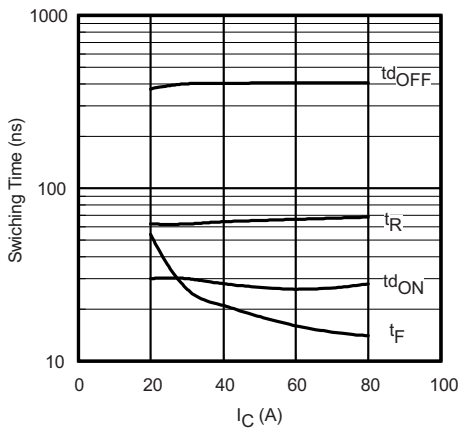


Fig. 14 - Typical Switching Time vs. I_C
 T_J = 125 °C; L = 250 μH; V_{CE} = 400 V
 R_g = 5 Ω; V_{GE} = 15 V

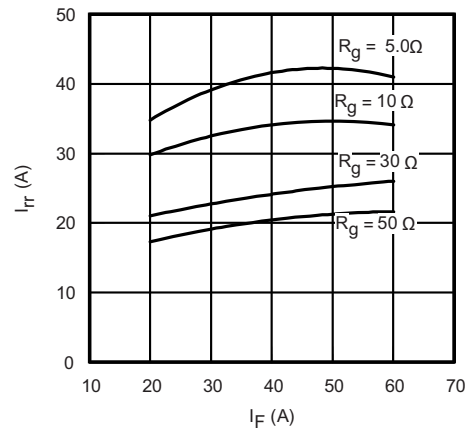


Fig. 17 - Typical Diode I_{rr} vs. I_F
 T_J = 125 °C

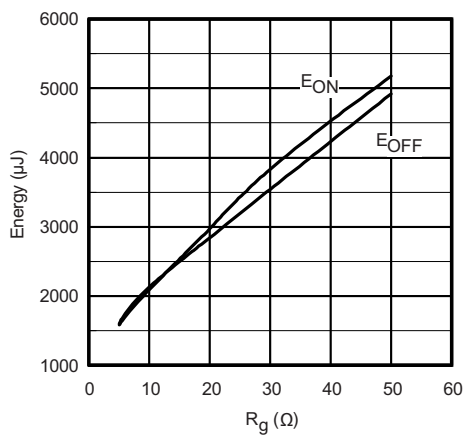


Fig. 15 - Typical Energy Loss vs. R_g
 T_J = 150 °C; L = 250 μH; V_{CE} = 600 V
 I_{CE} = 40 A; V_{GE} = 15 V

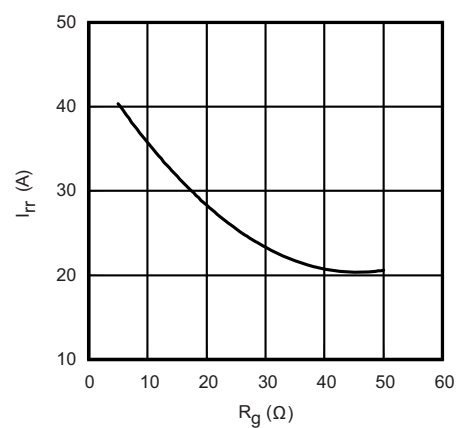


Fig. 18 - Typical Diode I_{rr} vs. R_g
 T_J = 125 °C; I_F = 40 A

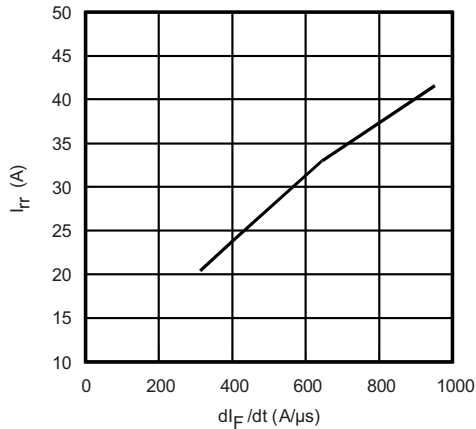


Fig. 19 - Typical Diode I_{rr} vs. dI_F/dt
 $V_{CC} = 600\text{ V}$; $V_{GE} = 15\text{ V}$; $I_{CE} = 40\text{ A}$; $T_J = 125\text{ }^\circ\text{C}$

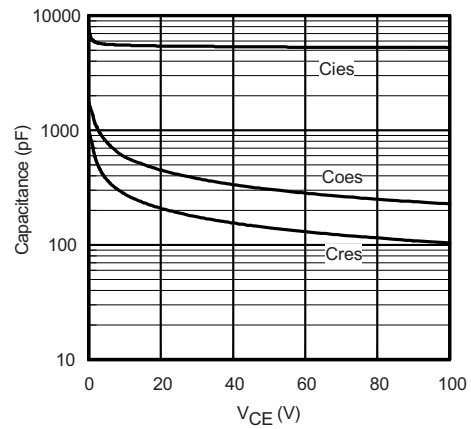


Fig. 21 - Typical Capacitance vs. V_{CE}
 $V_{GE} = 0\text{ V}$; $f = 1\text{ MHz}$

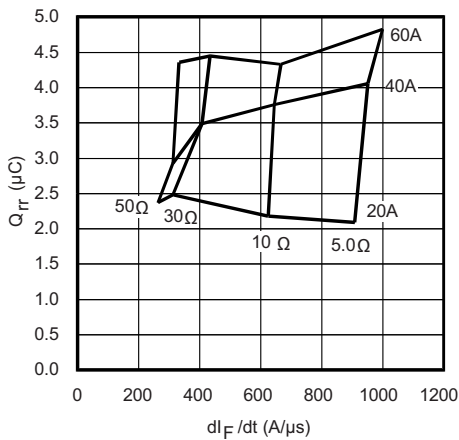


Fig. 20 - Typical Diode Q_{rr} vs. dI_F/dt
 $V_{CC} = 600\text{ V}$; $V_{GE} = 15\text{ V}$; $T_J = 125\text{ }^\circ\text{C}$

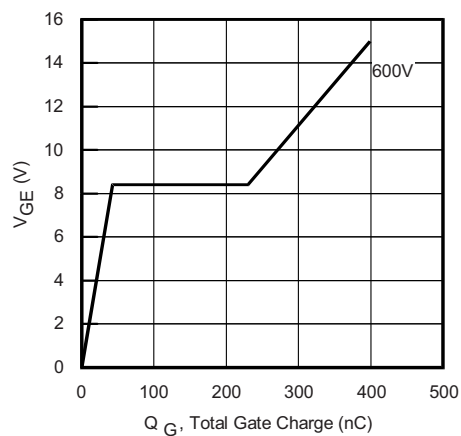


Fig. 22 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 5.0\text{ A}$; $L = 600\text{ }\mu\text{H}$

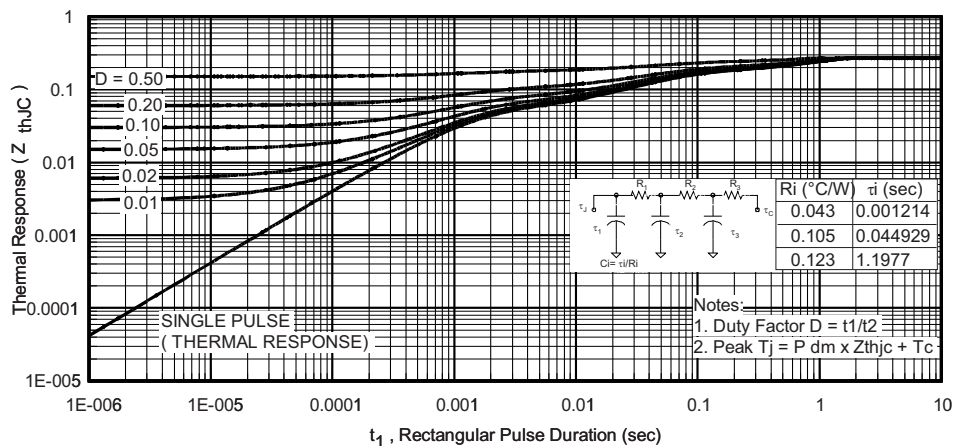


Fig. 23 - Maximum Transient Thermal Impedance, Junction to Case (IGBT)

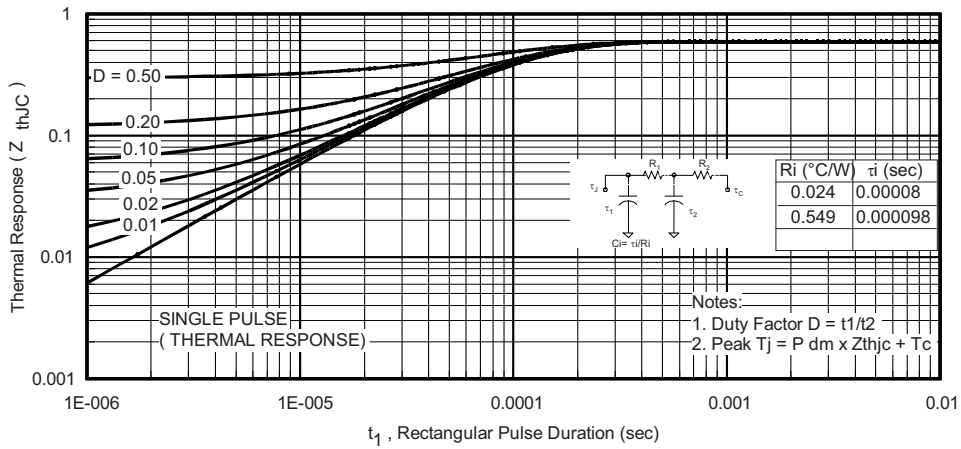


Fig. 24 - Maximum Transient Thermal Impedance, Junction to Case (Diode)

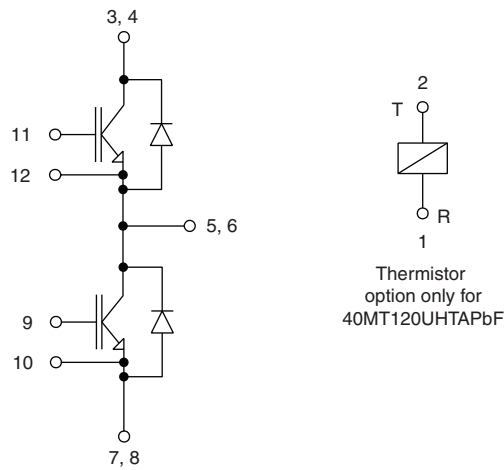


Fig. 25 - Electrical diagram

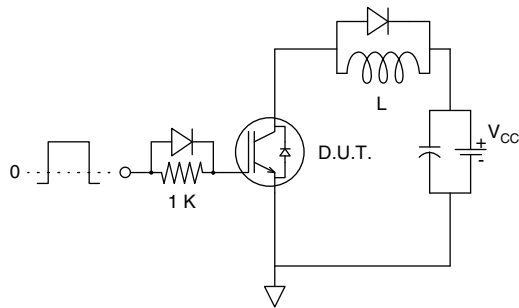


Fig. CT.1 - Gate Charge Circuit (Turn-Off)

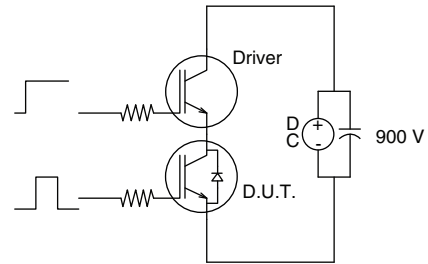


Fig. CT.3 - S.C. SOA Circuit

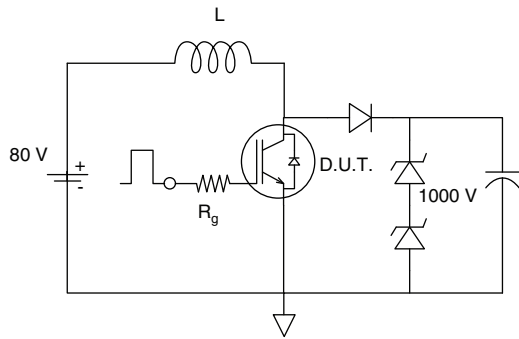


Fig. CT.2 - RBSOA Circuit

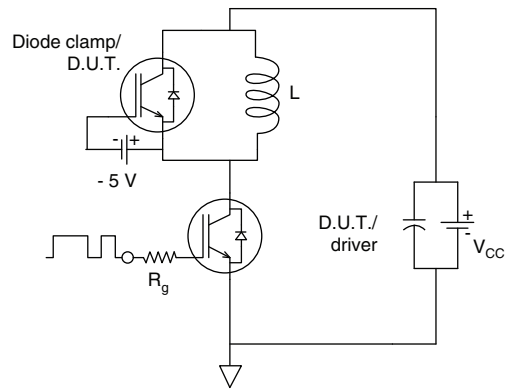


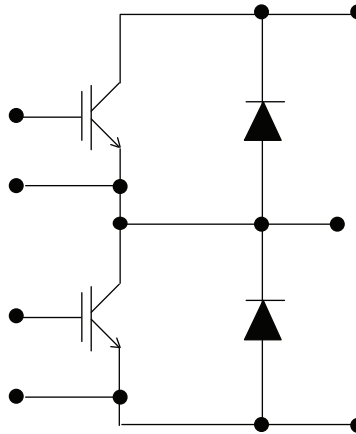
Fig. CT.4 - Switching Loss Circuit

ORDERING INFORMATION TABLE

Device code	VS-	40	MT	120	U	H	T	A	PbF
	①	②	③	④	⑤	⑥	⑦	⑧	⑨

- 1** - Vishay Semiconductors product
- 2** - Current rating (40 = 40 A)
- 3** - Essential part number
- 4** - Voltage code (120 = 1200 V)
- 5** - Speed/type (U = Ultrafast IGBT)
- 6** - Circuit configuration (H = Half bridge)
- 7** - Special option:
 - None = No special option
 - T = Thermistor
- 8** - A = Al₂O₃ DBC substrate
- 9** - PbF = Lead (Pb)-free

CIRCUIT CONFIGURATION



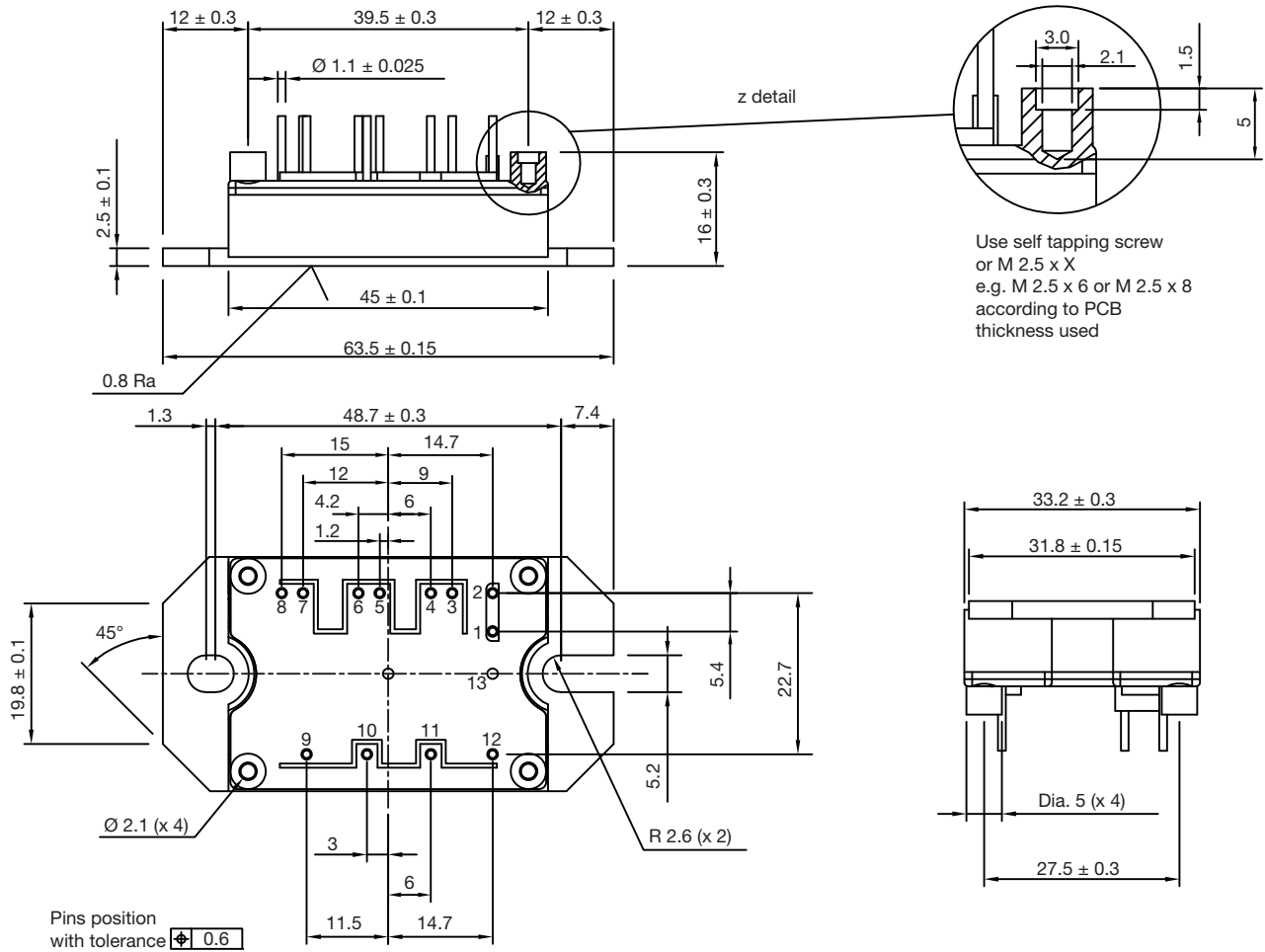
LINKS TO RELATED DOCUMENTS

Dimensions	www.vishay.com/doc?95175
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MTP

DIMENSIONS in millimeters



Use self tapping screw or M 2.5 x X e.g. M 2.5 x 6 or M 2.5 x 8 according to PCB thickness used

Note

- Unused terminals are not assembled in the package



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